

MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK31V60W5

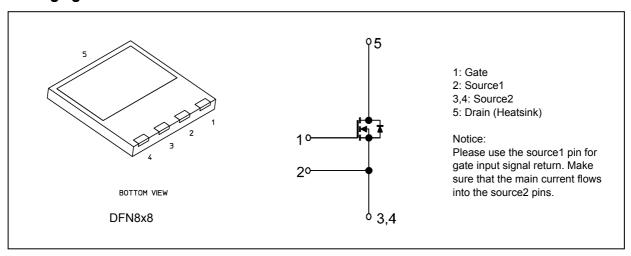
1. Applications

· Switching Voltage Regulators

2. Features

- (1) Fast reverse recovery time: $t_{rr} = 135$ ns (typ.)
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 0.087 \Omega(typ.)$
- (3) Easy to control Gate switching
- (4) Enhancement mode: V_{th} = 3 to 4.5 V (V_{DS} = 10 V, I_{D} = 1.5 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	600	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	30.8	Α
Drain current (pulsed)	(Note 1)	I _{DP}	123	
Power dissipation (T _c = 25 °C)	P _D	240	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	338	mJ
Avalanche current		I _{AR}	7.7	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	30.8	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	123	1
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150]

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.52	°C/W

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 10 mH, R_G = 25 Ω , I_{AR} = 7.7 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1.5 mA	3	_	4.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 15.4 A	_	0.087	0.109	Ω

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	$V_{DS} = 300 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}$	_	3000	_	pF
Reverse transfer capacitance	C _{rss}		_	9.5	_	
Output capacitance	C _{oss}		_	70	_	
Effective output capacitance	C _{o(er)}	V _{DS} = 0 to 400 V, V _{GS} = 0 V	_	123	_	
Gate resistance	r _g	V _{DS} = OPEN , f = 1 MHz	_	2	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	80	_	ns
Switching time (turn-on time)	t _{on}		_	120	_	
Switching time (fall time)	t _f		_	8.5	_	
Switching time (turn-off time)	t _{off}		_	165	_	
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 7.7 A	50	_	_	V/ns

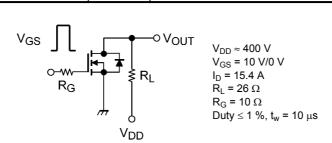


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30.8 \text{ A}$		105		nC
Gate-source charge 1	Q _{gs1}			24	_	
Gate-drain charge	Q_{gd}			65		

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 30.8 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 15.4 A, V _{GS} = 0 V	_	135	220	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 100 A/μs	_	0.6	_	μС
Peak reverse recovery current	I _{rr}		_	10	_	Α
Diode dv/dt ruggedness	dv/dt	I _{DR} = 15.4 A, V _{GS} = 0 V, V _{DD} = 400 V	50	_	_	V/ns



7. Marking

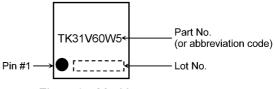


Fig. 7.1 Marking



8. Characteristics Curves (Note)

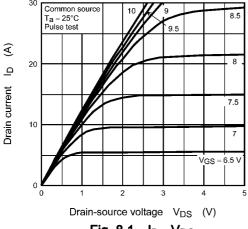
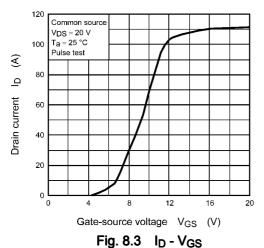
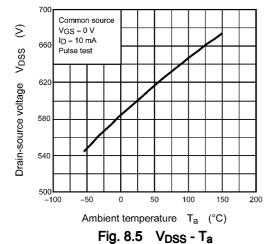
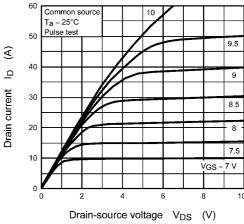


Fig. 8.1 I_D - V_{DS}



rig. 6.5 ip - vgs





TK31V60W5

Fig. 8.2 I_D - V_{DS}

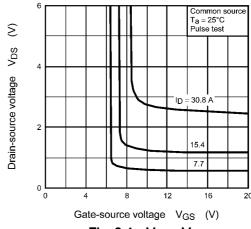


Fig. 8.4 V_{DS} - V_{GS}

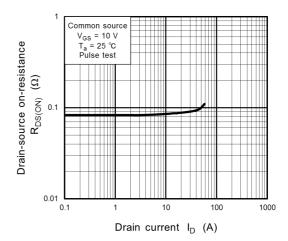


Fig. 8.6 $R_{DS(ON)}$ - I_D

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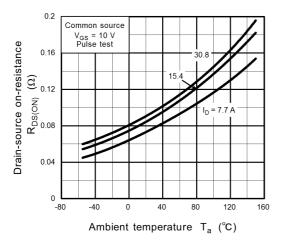
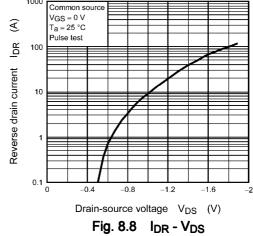


Fig. 8.7 R_{DS(ON)} - T_a



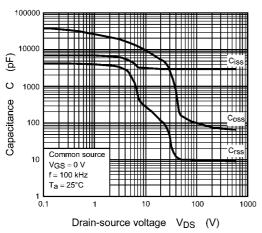


Fig. 8.9 C - V_{DS}

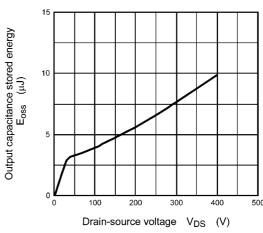


Fig. 8.10 Eoss - VDS

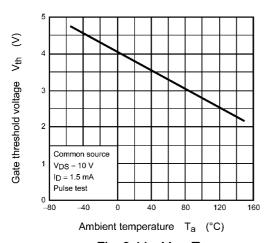


Fig. 8.11 V_{th} - T_a

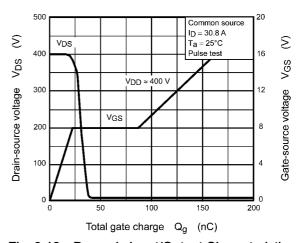


Fig. 8.12 Dynamic Input/Output Characteristics

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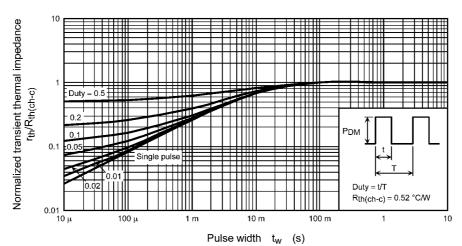


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

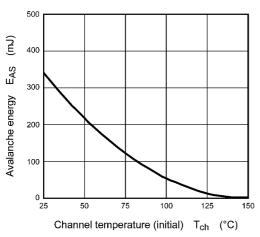


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

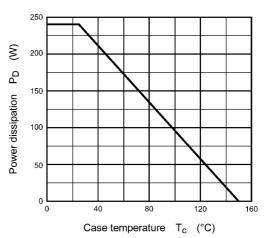


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

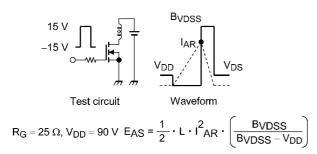


Fig. 8.16 Test Circuit/Waveform

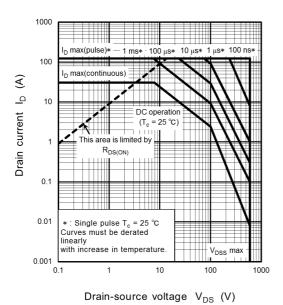


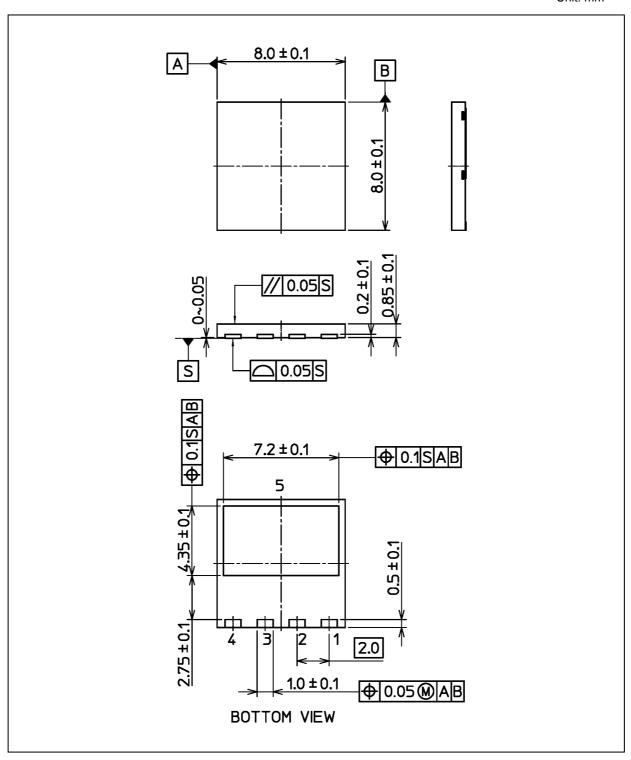
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.175 g (typ.)

	Package Name(s)
TOSHIBA: 2-8T1A	
Nickname: DFN8x8	

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